

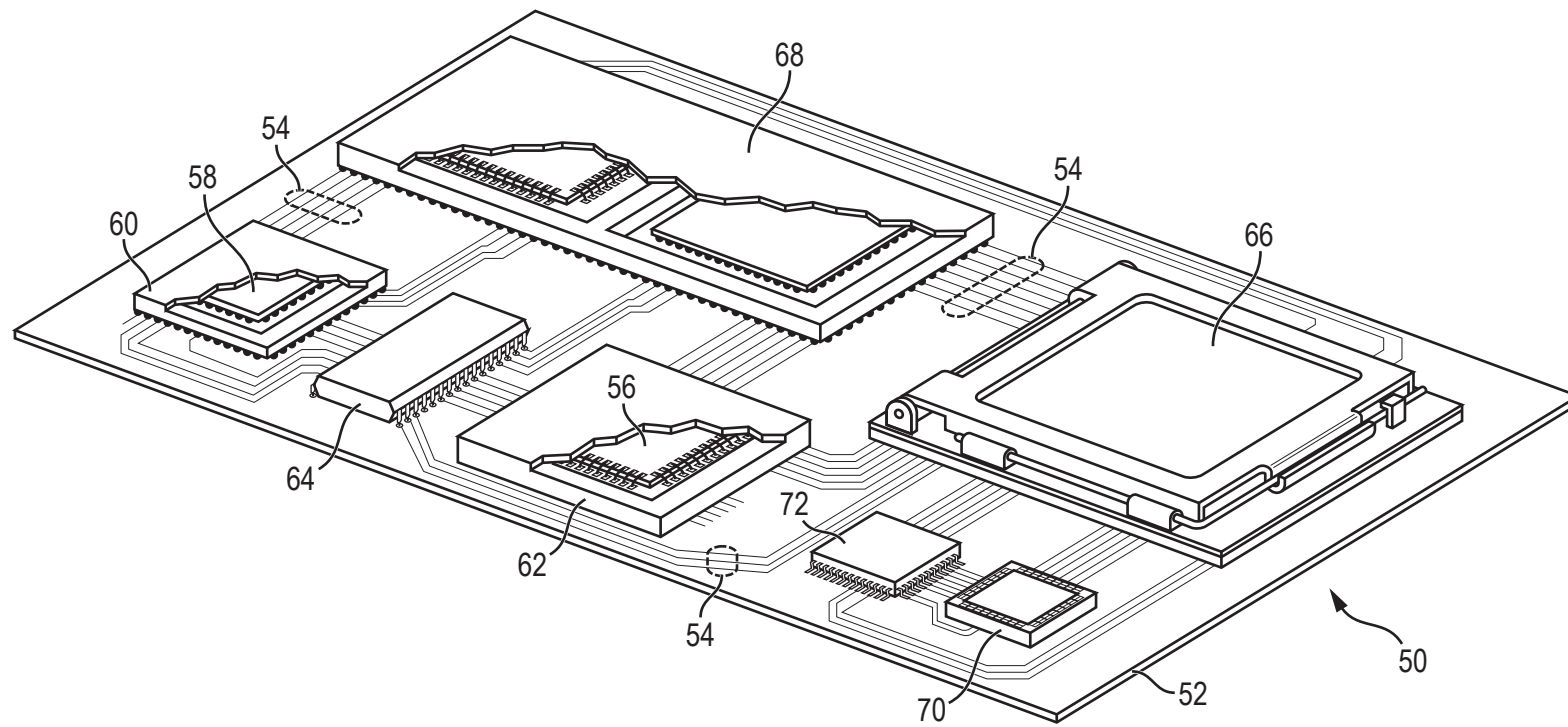


FIG. 1

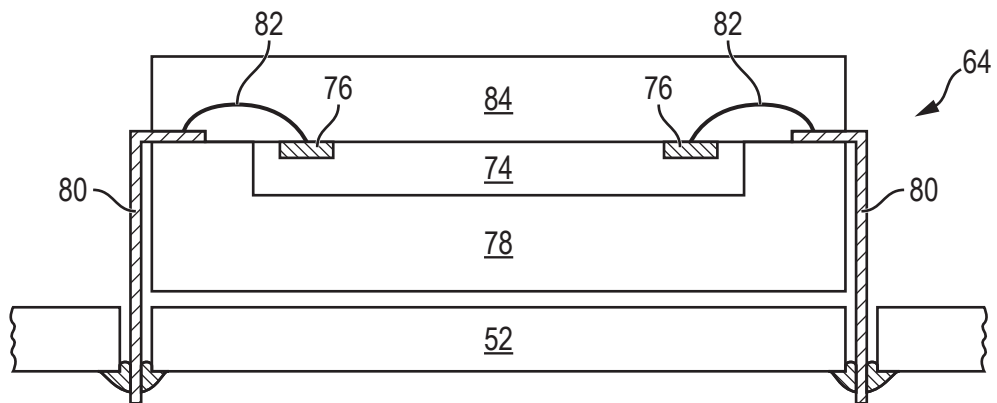


FIG. 2a

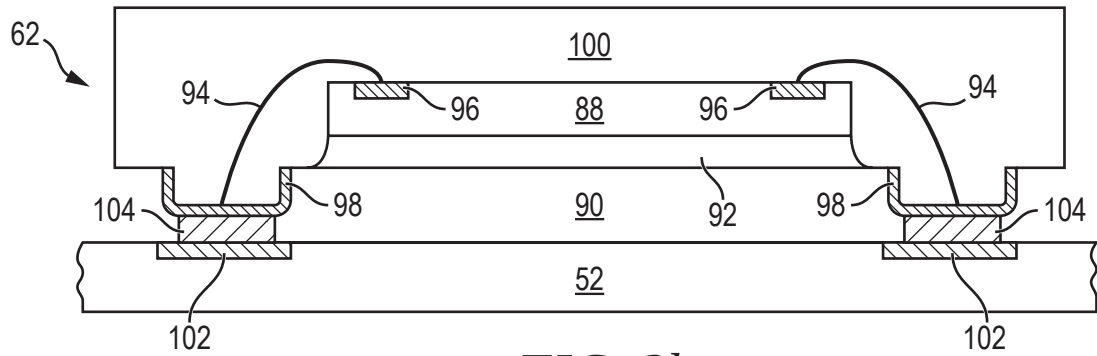


FIG. 2b

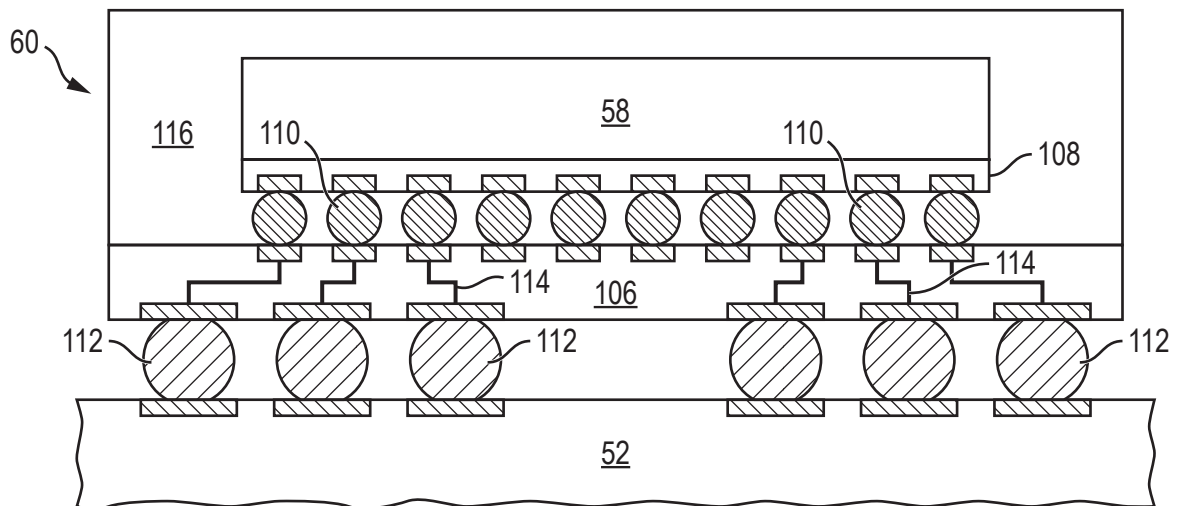


FIG. 2c

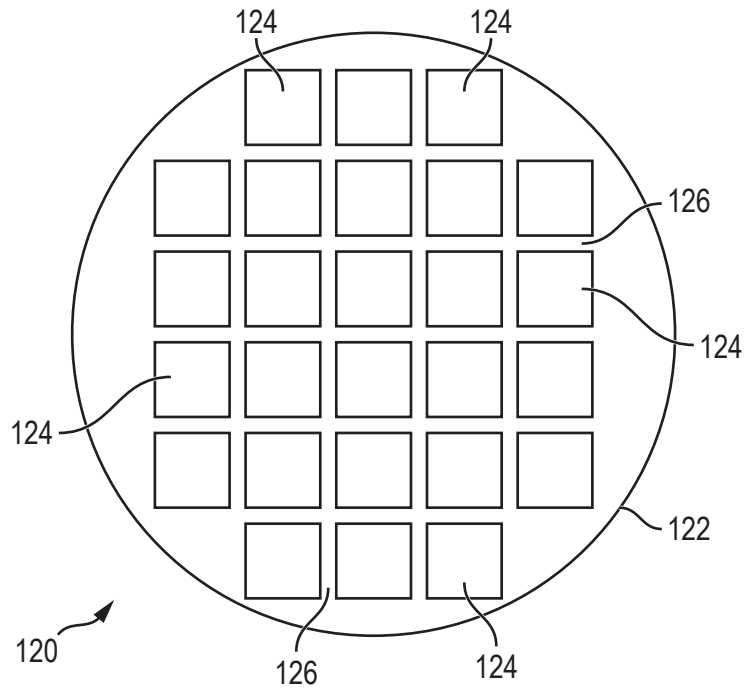


FIG. 3a

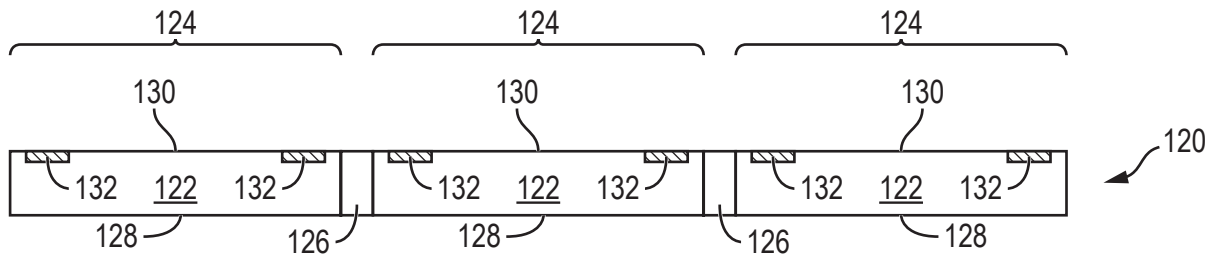


FIG. 3b

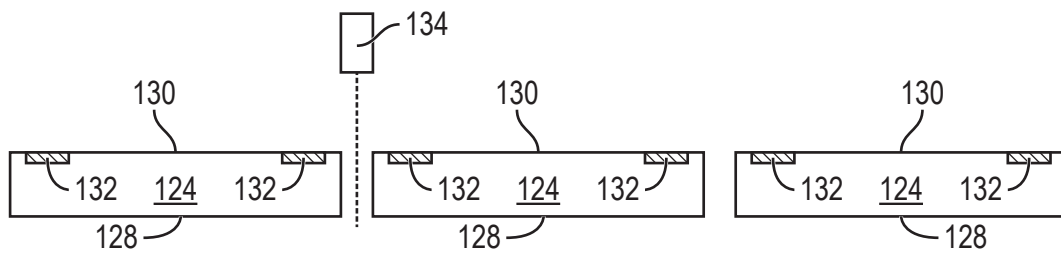


FIG. 3c

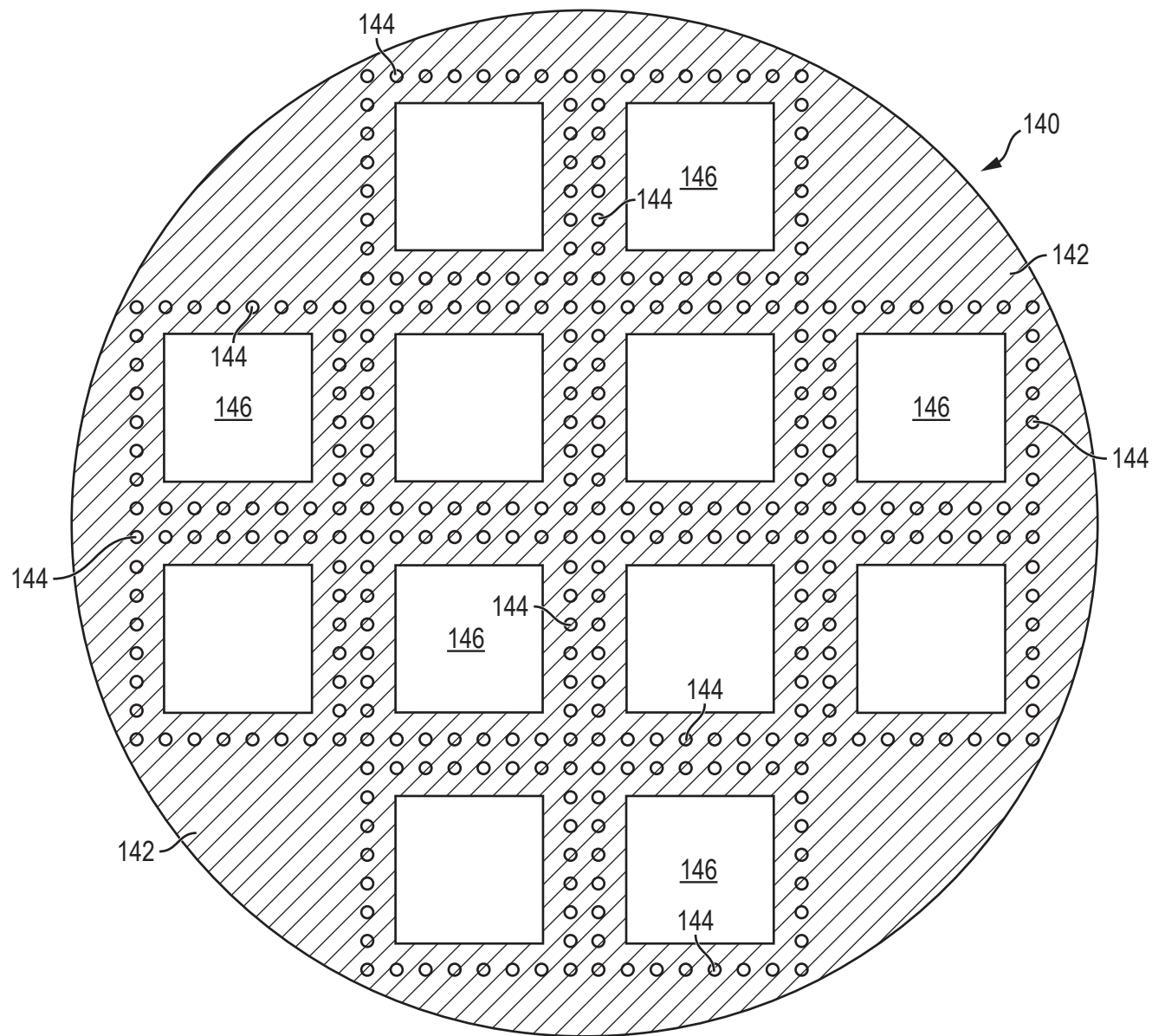


FIG. 4

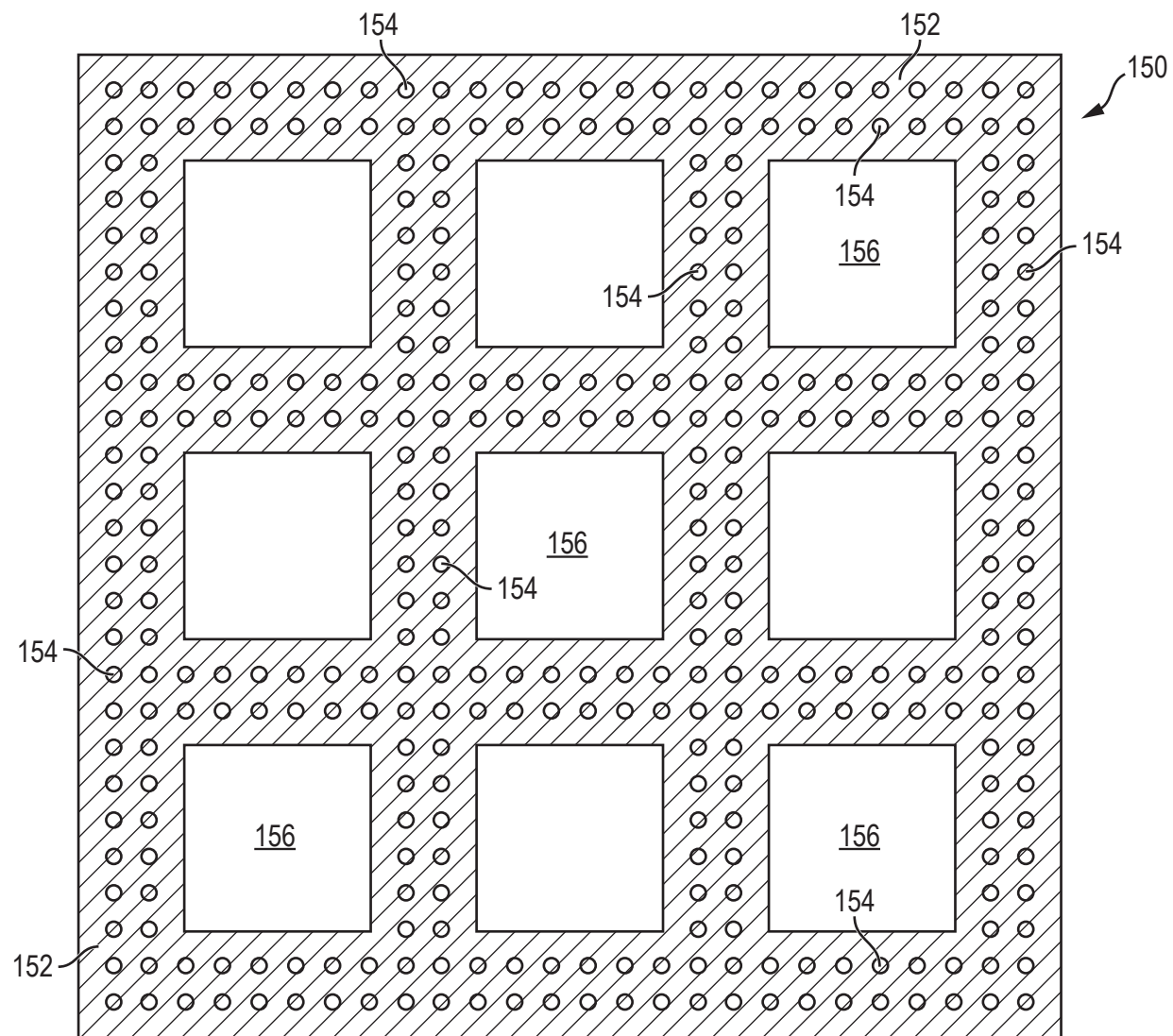


FIG. 5

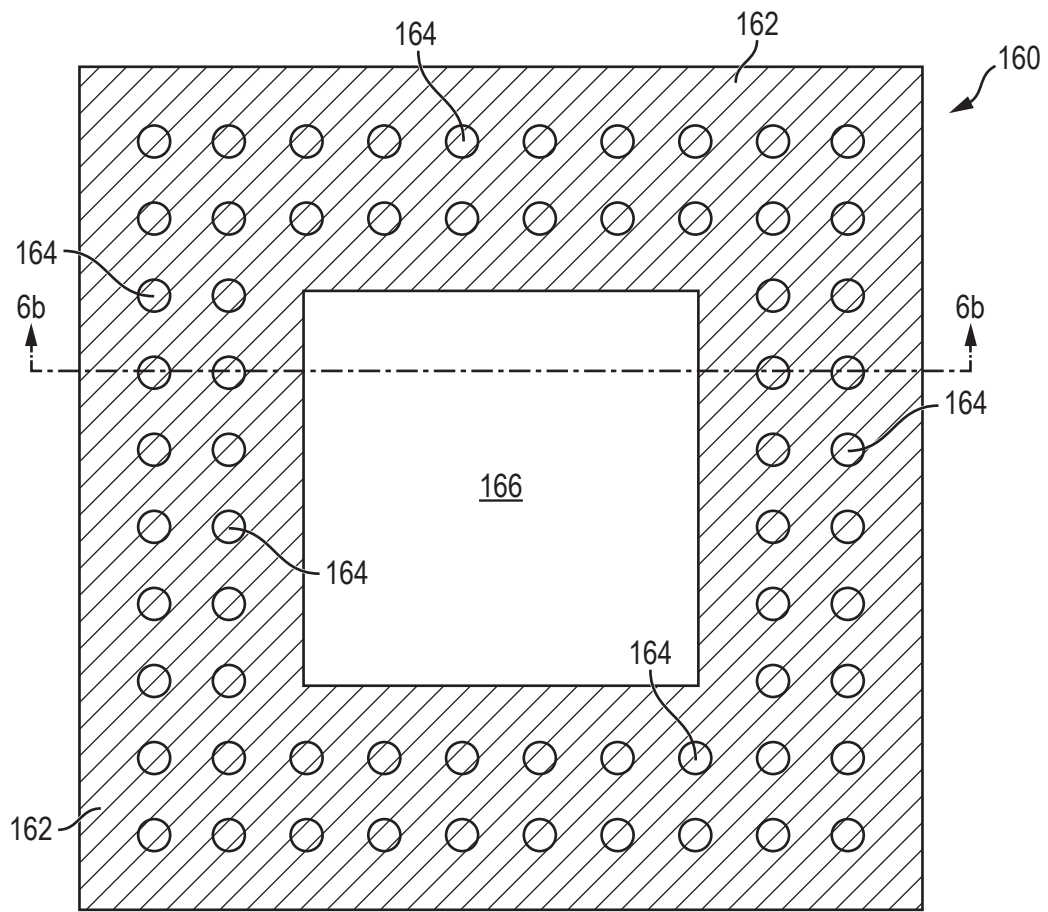


FIG. 6a

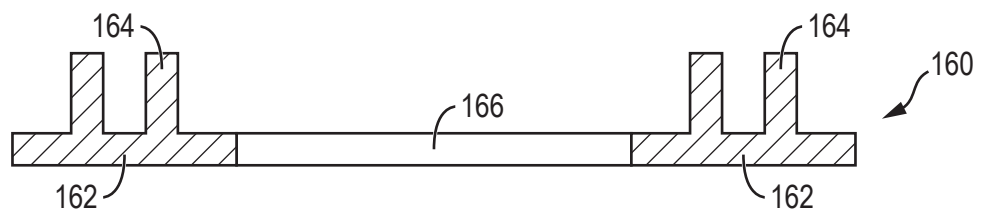


FIG. 6b

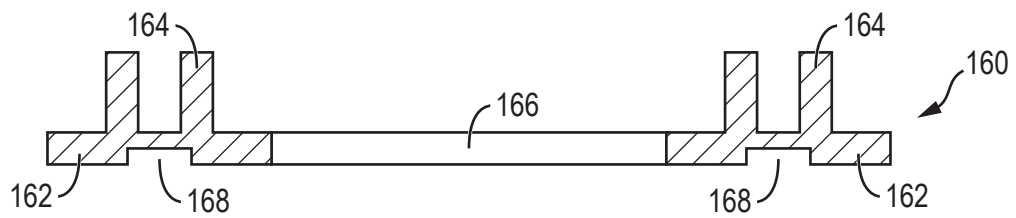
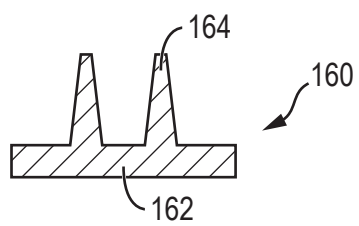
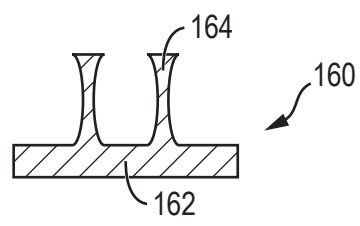


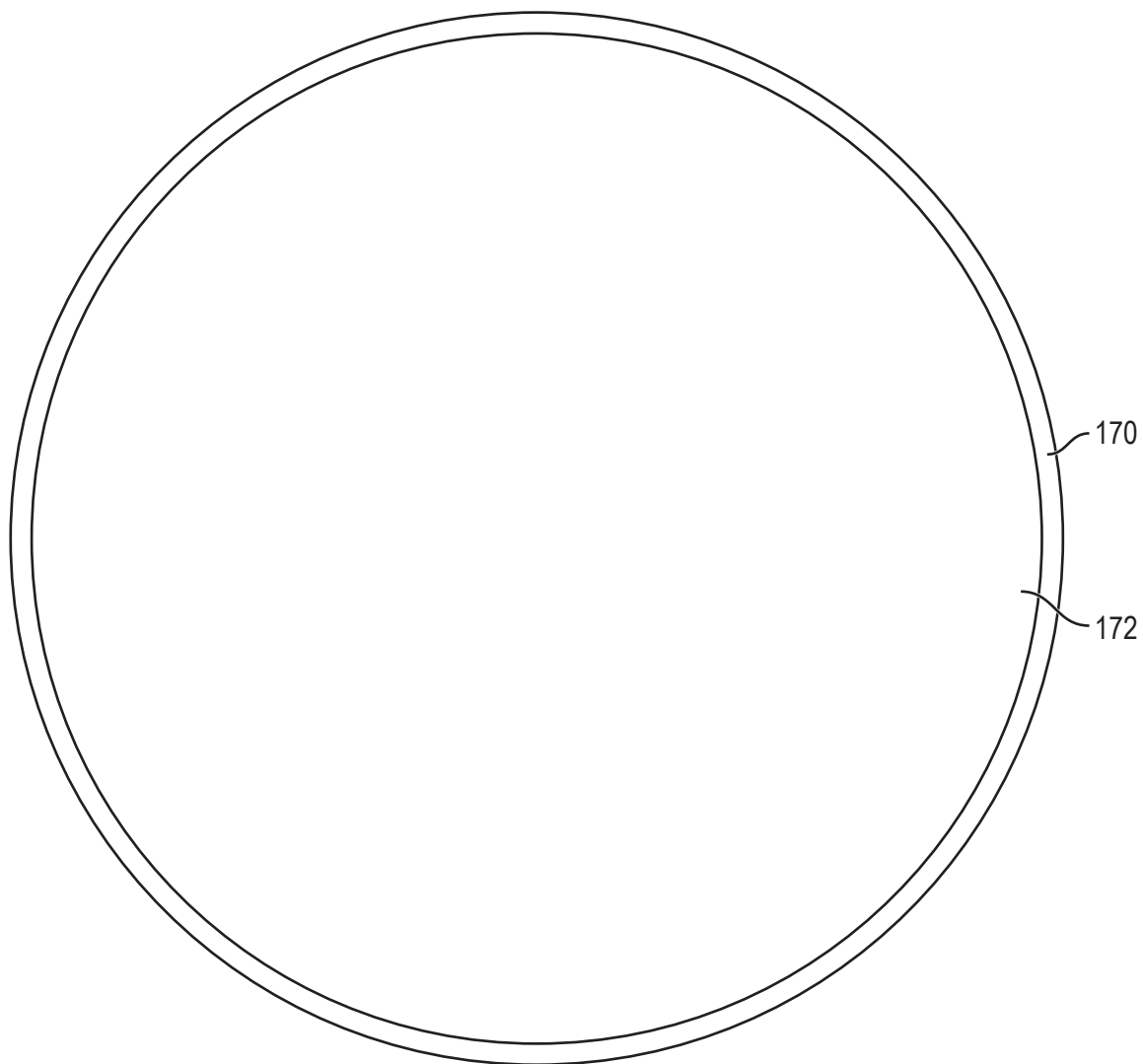
FIG. 6c



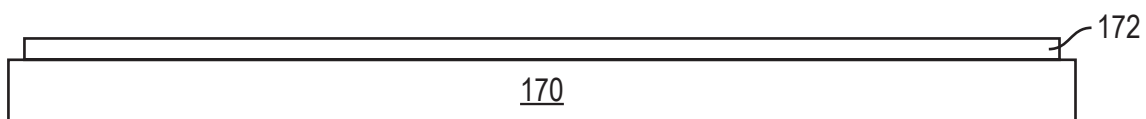
*FIG. 7a*



*FIG. 7b*



*FIG. 8a*



*FIG. 8b*

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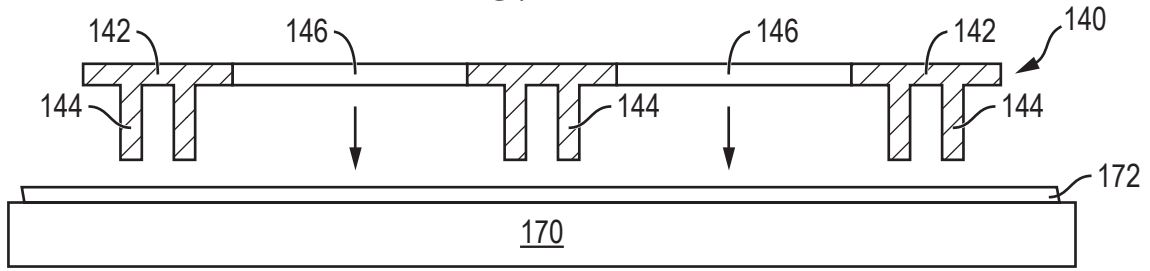


FIG. 8c

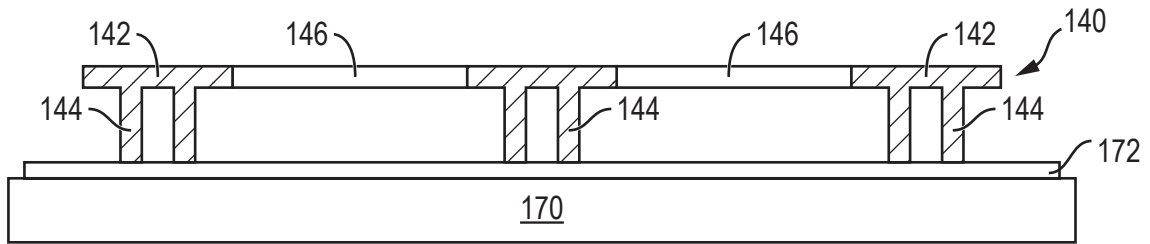


FIG. 8d

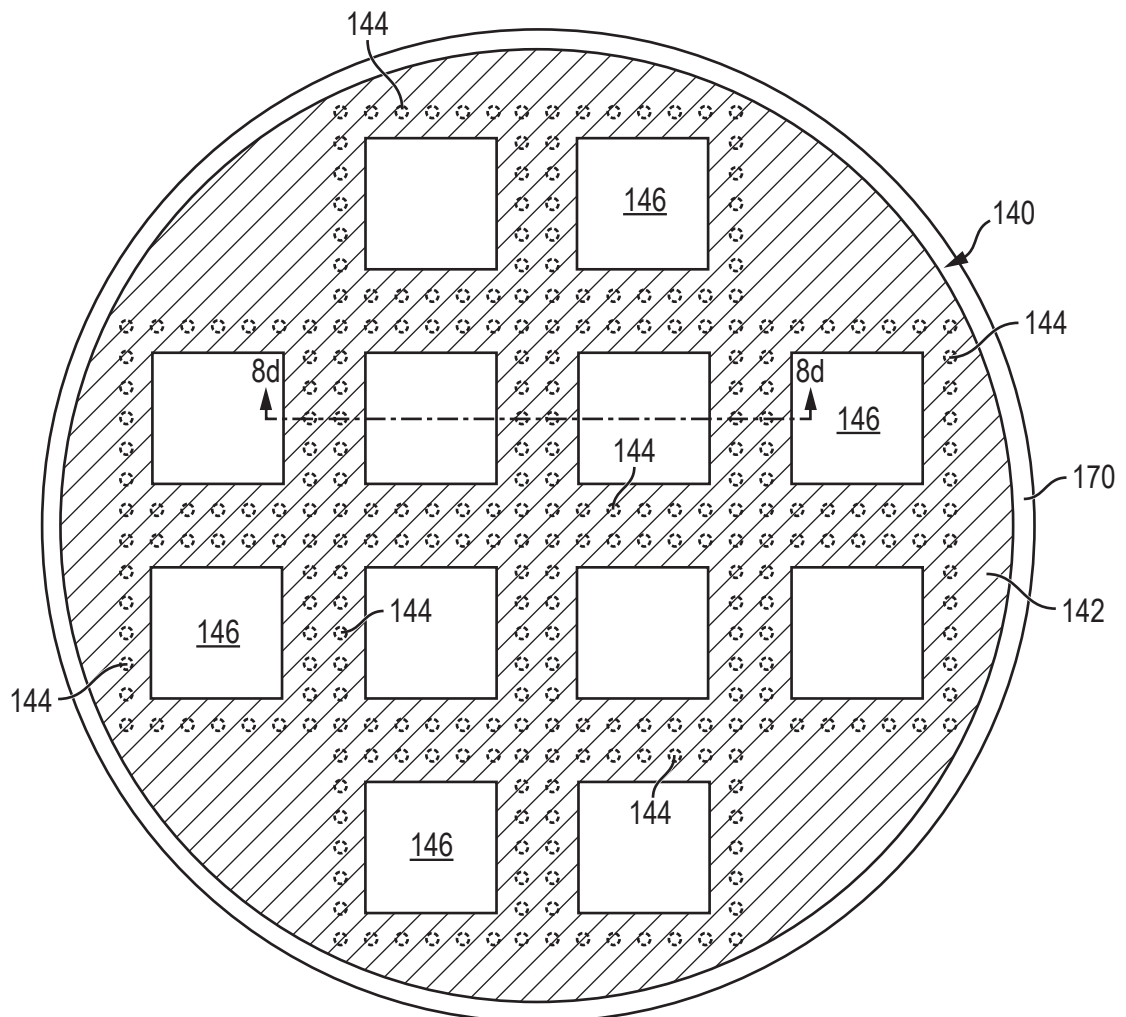


FIG. 8e

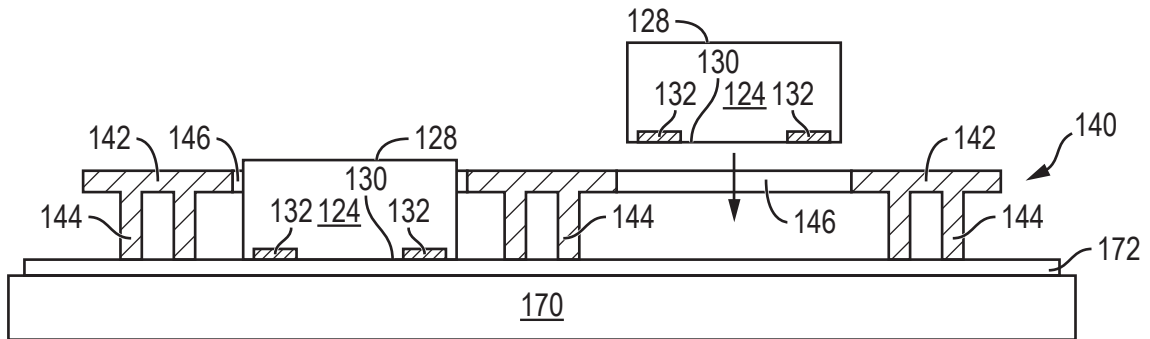


FIG. 8f

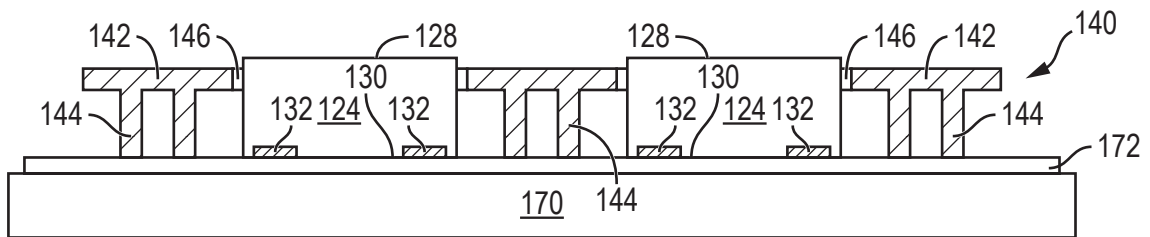


FIG. 8g

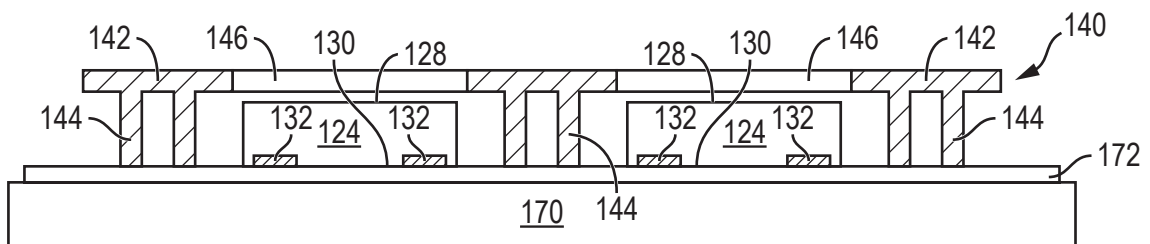


FIG. 8h

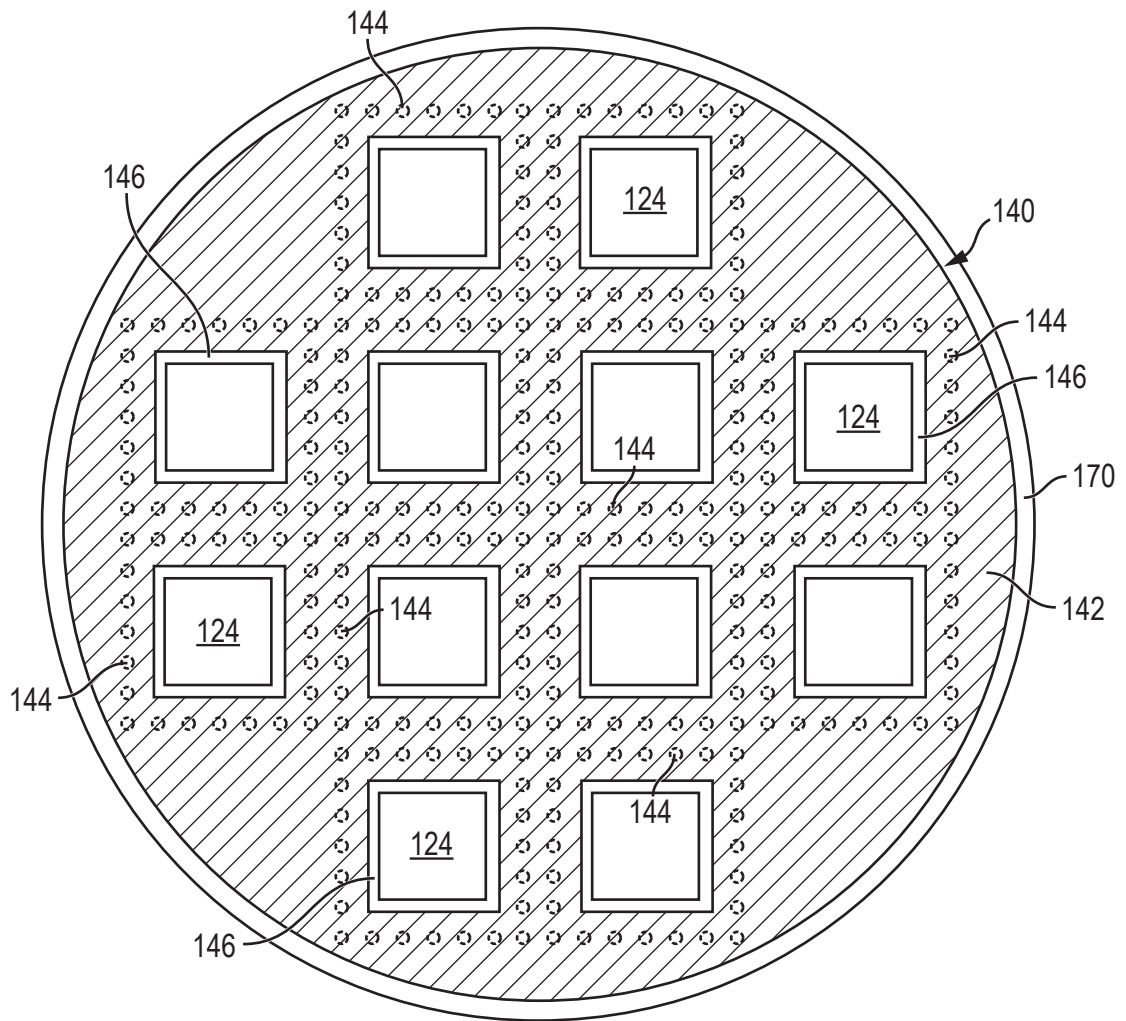


FIG. 8i

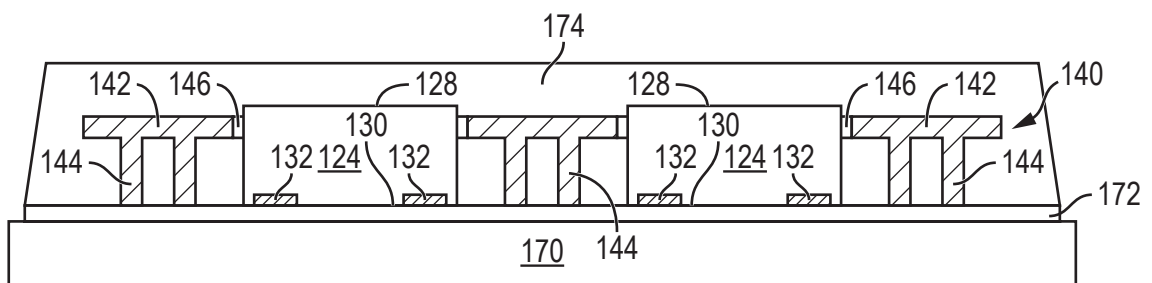


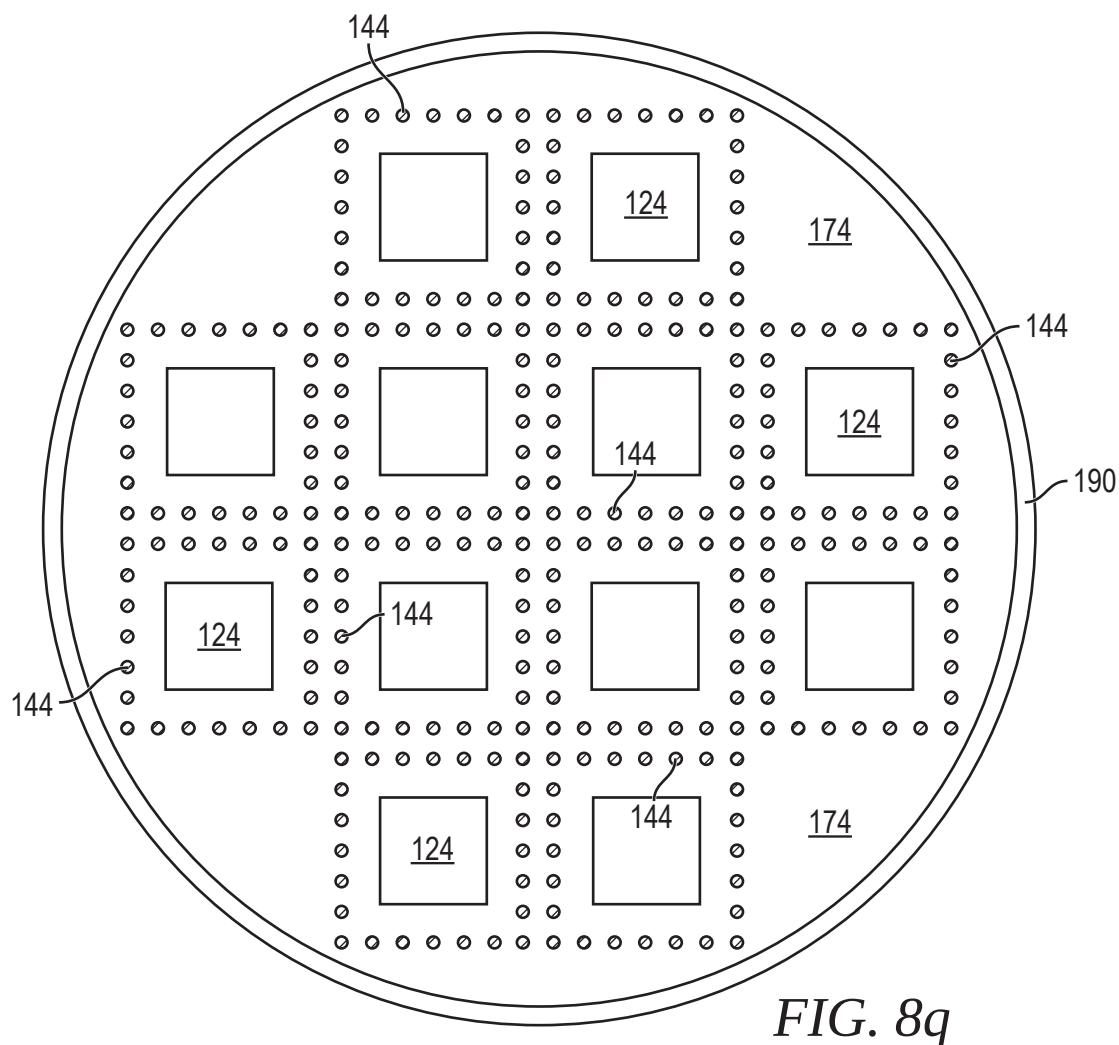
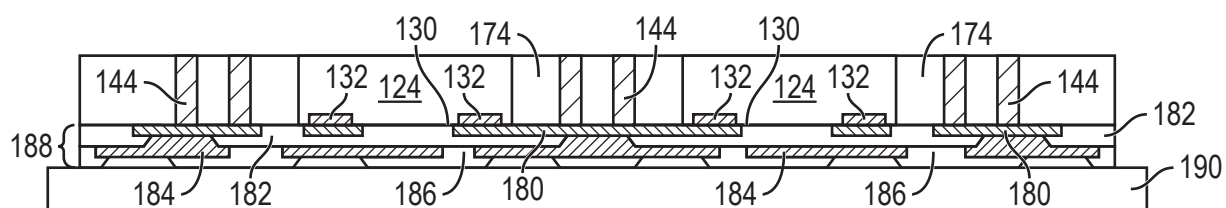
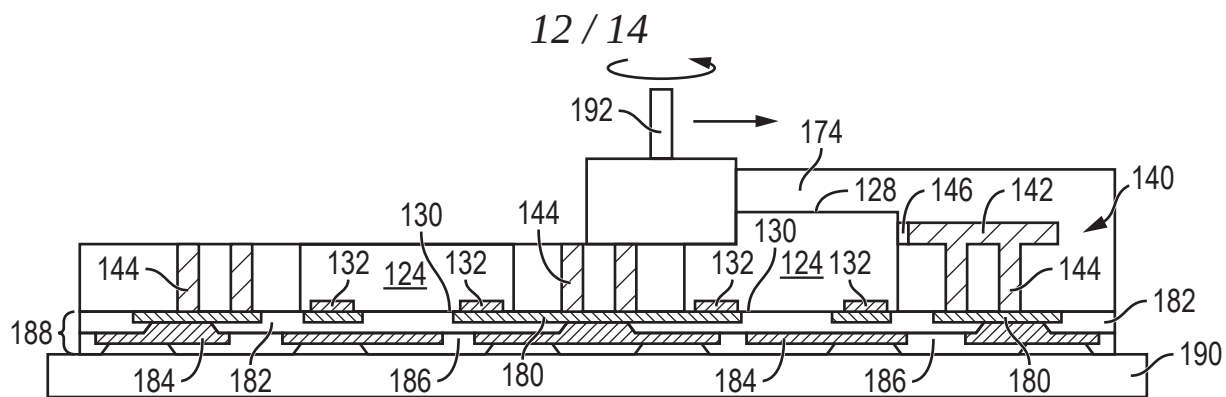
FIG. 8j

A cross-sectional view of a semiconductor device 174. The device features a substrate 140 with a top layer 128. A central region contains a stack of layers 130, 124, and 132. This central region is flanked by two sets of structures, each consisting of a layer 146 on top of a layer 142, which is further supported by a layer 144. The entire structure is labeled 174.

[illegible]

This cross-sectional view shows a semiconductor device with a multi-layered structure. A substrate 190 is at the base, with a series of layers 180, 186, 182, and 184 stacked on top. A bracket 188 groups these four layers. Above the 184 layer is a thin layer 174. The top surface features a series of repeating structures. Each structure includes a central rectangular block 130, flanked by smaller rectangular blocks 144. On top of block 130 is a layer 128, which has a central portion 124 and side portions 132. The side portions 132 are separated from the substrate by a gap 146. The entire structure is enclosed within a frame 140.

FIG. 8n



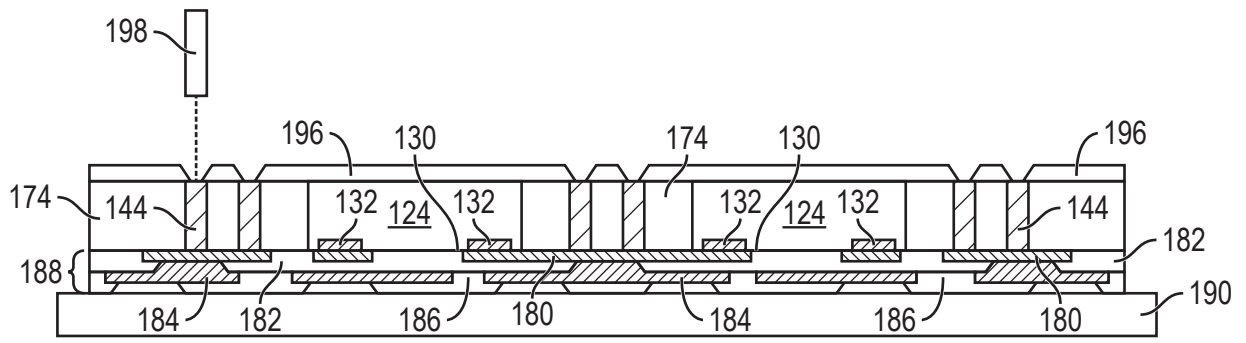


FIG. 8r

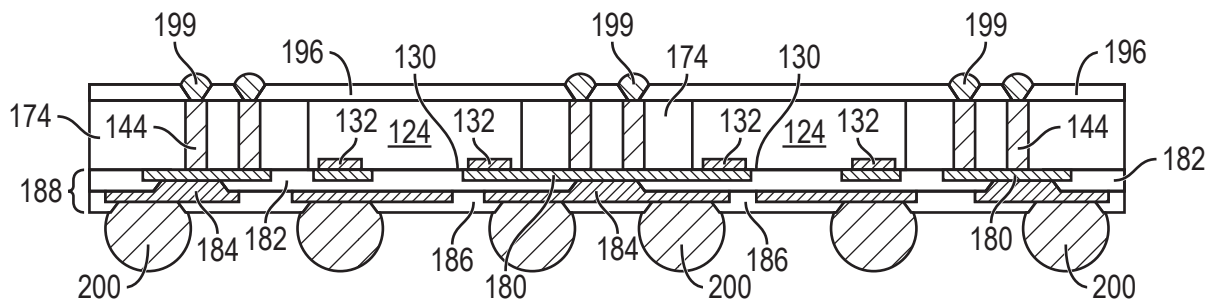


FIG. 8s

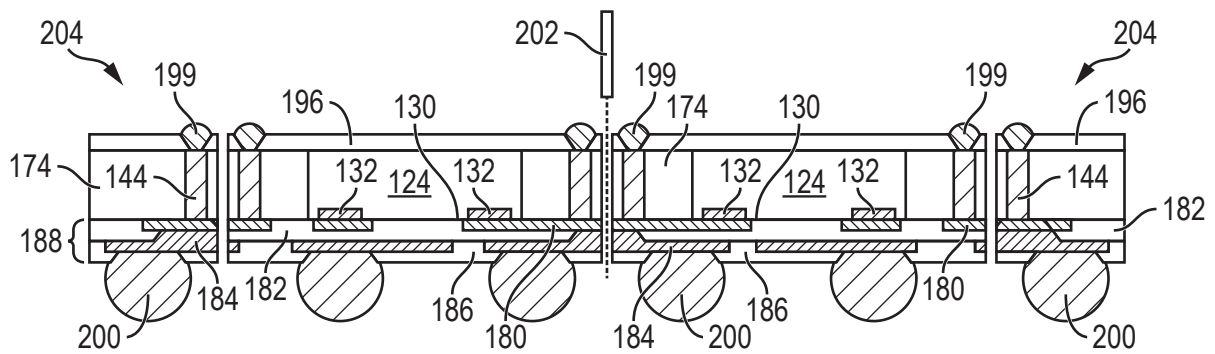


FIG. 8t

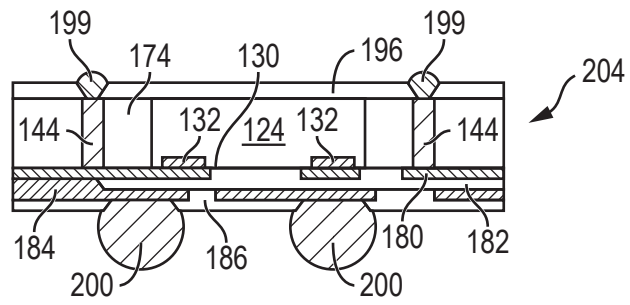


FIG. 9

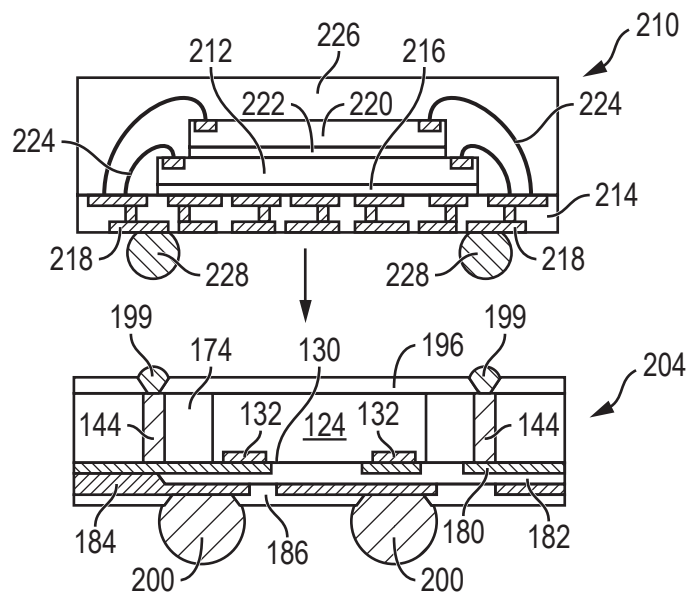


FIG. 10a

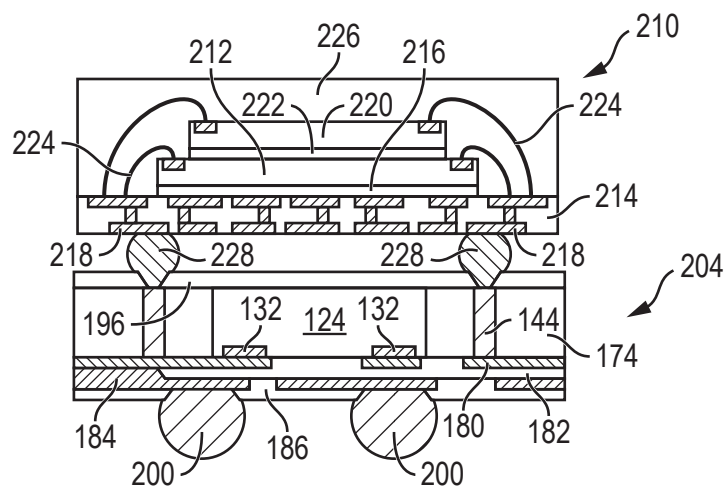


FIG. 10b